TOSHIBA Transistor Silicon NPN Epitaxial Type

TPCP8504

High Speed Switching Applications DC-DC Converter Applications

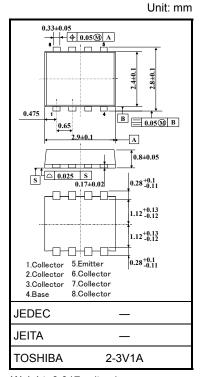
• High DC current gain : hFE = 400 to 1000 (IC = 0.2 A)

• Low collector-emitter saturation : $V_{CE (sat)} = 0.12 \text{ V (max)}$

• High-speed switching : $t_f = 25$ ns (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	20	V	
Collector-emitter voltage		V _{CEO}	10	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC (Note 1)	Ic	2.0	А	
	Pulse (Note 1)	I _{CP}	3.5		
Base current		Ι _Β	0.2	Α	
Collector power dissipation (Note 2)	t = 10s	Pc	2.8	W	
	DC	FC	1.2		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



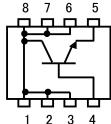
Weight: 0.017 g (typ.)

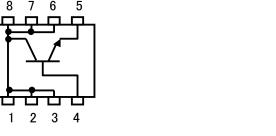
- Note 1: Please use devices on condition that the junction temperature is below 150°C.
- Note 2: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)
- Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

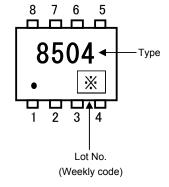
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Figure 1. Circuit configuration (top view)

Figure 2. Marking (Note 4)

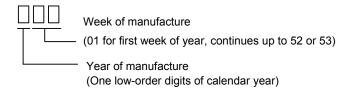






Note 4: ● on lower left on the marking indicates Pin 1.

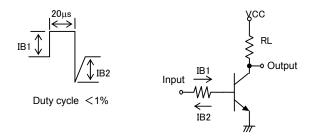
Weekly code: (Three digits)

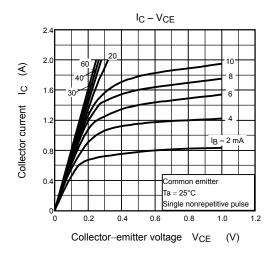


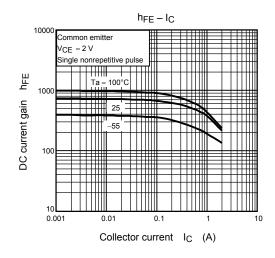
Electrical Characteristics (Ta = 25°C)

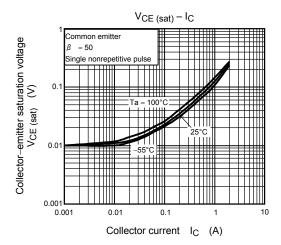
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$	_	_	100	nA
Emitter cut-off current		I _{EBO}	V _{EB} = 7 V, I _C = 0	_	_	100	nA
Collector-emitter breakdown voltage		V (BR) CEO	$I_C = 10 \text{ mA}, I_B = 0$	10	_	_	V
DC current gain		h _{FE} (1)	$V_{CE} = 2 \text{ V}, I_{C} = 0.2 \text{ A}$	400	_	1000	
		h _{FE} (2)	V _{CE} = 2 V, I _C = 0.6 A	200	_	_	
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 0.6 A, I _B = 12 mA	_	_	0.12	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = 0.6 A, I _B = 12 mA	_	_	1.1	V
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1MHz	_	10	_	pF
Switching time	Rise time	t _r	See Figure 3 circuit diagram $V_{CC} \simeq 6 \text{ V}, \text{ R}_L = 10 \Omega$	_	60	_	ns
	Storage time	t _{stg}		_	215	_	
	Fall time	t _f	$I_{B1} = -I_{B2} = 12 \text{ mA}$	_	25	_	

Figure 3. Switching Time Test Circuit & Timing Chart

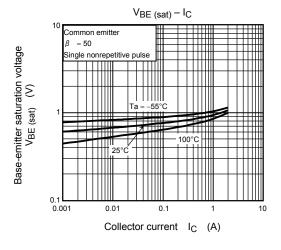


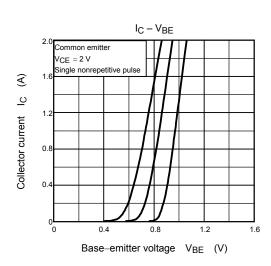




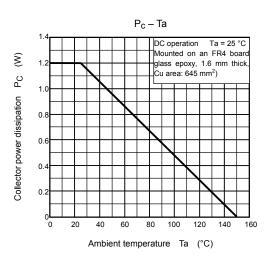


Ta = 100°C

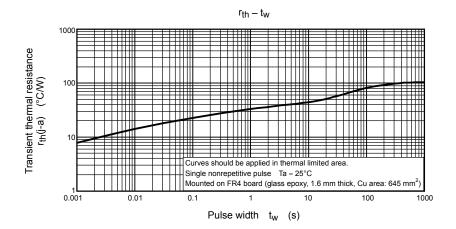


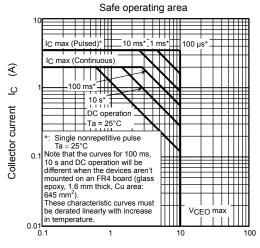


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Collector-emitter voltage V_{CE} (V)

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20070701-EN

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